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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/824,428	04/15/2004	James F. Buller	50432-702	6497	
7590	11/10/2004	EXAMINER			
McDermott, Will & Emery 600 13th Street, N.W. Washington, DC 20005-3096				VU, DAVID	
		ART UNIT	PAPER NUMBER	2818	

DATE MAILED: 11/10/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No.	Applicant(s)
	10/824,428	BULLER ET AL.
	Examiner	Art Unit
	DAVID VU	2818

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

1) Responsive to communication(s) filed on 15 October 2004.

2a) This action is **FINAL**. 2b) This action is non-final.

3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

4) Claim(s) 10-12 and 16-19 is/are pending in the application.
4a) Of the above claim(s) _____ is/are withdrawn from consideration.

5) Claim(s) _____ is/are allowed.

6) Claim(s) 10-12 and 16-19 is/are rejected.

7) Claim(s) _____ is/are objected to.

8) Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

9) The specification is objected to by the Examiner.

10) The drawing(s) filed on 04/15/04 is/are: a) accepted or b) objected to by the Examiner.

 Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).

 Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).

11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
a) All b) Some * c) None of:
1. Certified copies of the priority documents have been received.
2. Certified copies of the priority documents have been received in Application No. _____.
3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

1) Notice of References Cited (PTO-892)
2) Notice of Draftsperson's Patent Drawing Review (PTO-948)
3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date 04/15/04.
4) Interview Summary (PTO-413)
Paper No(s)/Mail Date. ____.
5) Notice of Informal Patent Application (PTO-152)
6) Other: ____.

DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

1. Claims 10-12, 15-16 and 19 are rejected under 35 U.S.C. 102(e) as being anticipated by Yu (US 6,506,650).

Regarding claims 10-12, 16 and 19, Yu in related text (Col. 3, Lines 7-39 and Col. 4, Lines 15-21) and figures (Figs. 1-4) discloses a method for fabricating a semiconductor device, comprising: forming a gate electrode 16 over a substrate 12 with a gate dielectric layer 20 therebetween; forming an oxide liner 26 on the side surfaces of the gate electrode 16 and the upper surface of the substrate 12; forming a nitride liner 28 on the oxide liner 26 and forming an oxide sidewall spacer 32 ($k < 3.9$) on the nitride liner 28; ion implantation to form shallow source /drain extensions 22 at a junction depth of about 100-250Å in the upper surface of the substrate 12, using the gate electrode 16 as a mask, before forming the composite liner.

Art Unit: 2818

2. Claims 10-12 and 16-18 are rejected under 35 U.S.C. 102(e) as being anticipated by Miles (US 6,235,597).

Regarding claims 1-8, 10-12 and 16-19, Miles in related text (Col. 2, Line 51-Col. 3, Line 27 and Col. 3, Lines 60-62) and figure (Fig. 1) discloses a method for fabricating a semiconductor device, comprising: forming a gate electrode 3 over a substrate 1 with a gate dielectric layer 2 therebetween; forming an oxide liner 4 on the side surfaces of the gate electrode 3 and the upper surface of the substrate 1; forming a nitride liner 5 on the oxide liner 4 and forming an oxide sidewall spacer 6 on the nitride liner 5; ion implantation to form shallow source /drain extensions 10 at a junction depth of about 0.1 μ m by using p-type dopants such as boron in the upper surface of the substrate 1, using the gate electrode 3 as a mask, before forming the composite liner.

Conclusion

3. Any inquiry concerning this communication or earlier communications from the examiner should be directed to David Vu whose telephone number is (571) 272-1798. The examiner can normally be reached on Monday-Friday from 8:00am to 5:00pm. If attempt to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Nelms can be reached on (571) 272-1787. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR, Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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David Vu

November 06, 2004.